

December 2001

Features

- Logic Level Gate Drive
- Internal Voltage Clamp
- ESD Gate Protection
- $T_J = 175^{\circ}\text{C}$
- Ignition Energy Capable

Description

This N-Channel IGBT is a MOS gated, logic level device which is intended to be used as an ignition coil driver in automotive ignition circuits. Unique features include an active voltage clamp between the collector and the gate which provides Self Clamped Inductive Switching (SCIS) capability in ignition circuits. Internal diodes provide ESD protection for the logic level gate. Both a series resistor and a shunt resistor are provided in the gate circuit.

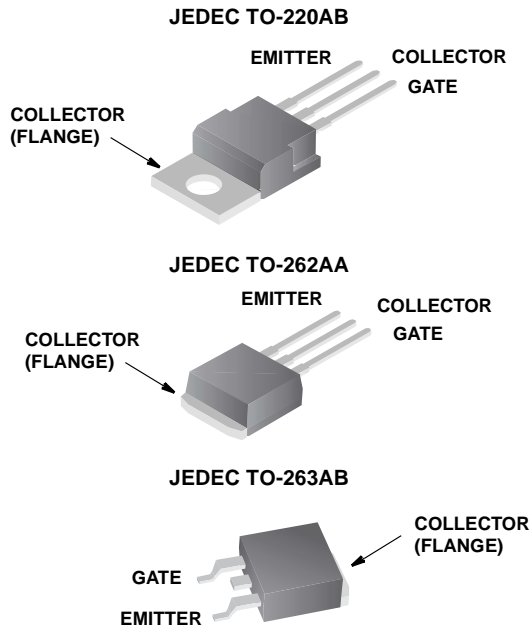
PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
HGTP20N35G3VL	T0-220AB	20N35GVL
HGT1S20N35G3VL	T0-262AA	20N35GVL
HGT1S20N35G3VLS	T0-263AB	20N35GVL

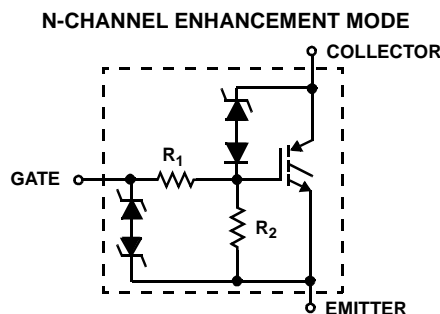
NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in the tape and reel, i.e., HGT1S20N35G3VLS9A.

The development type number for this device is TA49076.

Packages



Terminal Diagram



Absolute Maximum Ratings $T_C = +25^{\circ}\text{C}$, Unless Otherwise Specified

	HGTP20N35G3VL HGT1S20N35G3VL HGT1S20N35G3VLS	UNITS
Collector-Emitter Bkdn Voltage At 10mA, $R_{GE} = 1\text{k}\Omega$	375	V
Emitter-Collector Bkdn Voltage At 10mA	24	V
Collector Current Continuous At $V_{GE} = 5.0\text{V}$, $T_C = +25^{\circ}\text{C}$, Figure 7	20	A
At $V_{GE} = 5.0\text{V}$, $T_C = +100^{\circ}\text{C}$	20	A
Gate-Emitter-Voltage (Note)	± 10	V
Inductive Switching Current At $L = 2.3\text{mH}$, $T_C = +25^{\circ}\text{C}$	26	A
At $L = 2.3\text{mH}$, $T_C = +175^{\circ}\text{C}$	18	A
Collector to Emitter Avalanche Energy At $L = 2.3\text{mH}$, $T_C = +25^{\circ}\text{C}$	775	mJ
Power Dissipation Total At $T_C = +25^{\circ}\text{C}$	150	W
Power Dissipation Derating $T_C > +25^{\circ}\text{C}$	1.0	W/ $^{\circ}\text{C}$
Operating and Storage Junction Temperature Range	-40 to +175	$^{\circ}\text{C}$
Maximum Lead Temperature for Soldering	260	$^{\circ}\text{C}$
Electrostatic Voltage at 100pF, 1500 Ω	6	KV

NOTE: May be exceeded if I_{GEM} is limited to 10mA.

Specifications HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	LIMITS			UNITS	
			MIN	TYP	MAX		
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C = 10\text{mA}$, $V_{GE} = 0\text{V}$	$T_C = +175^\circ\text{C}$	310	345	380	V
			$T_C = +25^\circ\text{C}$	320	350	380	V
			$T_C = -40^\circ\text{C}$	320	355	390	V
Collector-Emitter Breakdown Voltage	BV_{CER}	$I_C = 10\text{mA}$ $V_{GE} = 0\text{V}$ $R_{GE} = 1\text{k}\Omega$	$T_C = +175^\circ\text{C}$	300	340	375	V
			$T_C = +25^\circ\text{C}$	315	345	375	V
			$T_C = -40^\circ\text{C}$	315	350	390	V
Gate-Emitter Plateau Voltage	V_{GEP}	$I_C = 10\text{A}$ $V_{CE} = 12\text{V}$	$T_C = +25^\circ\text{C}$	-	3.7	-	V
Gate Charge	$Q_{G(ON)}$	$I_C = 10\text{A}$ $V_{GE} = 5\text{V}$ $V_{CE} = 12\text{V}$	$T_C = +25^\circ\text{C}$	-	28.7	-	nC
Collector-Emitter Clamp Bkdn. Voltage	$BV_{CE(CL)}$	$I_C = 10\text{A}$ $R_G = 0\Omega$	$T_C = +175^\circ\text{C}$	325	360	395	V
Emitter-Collector Breakdown Voltage	BV_{ECS}	$I_C = 10\text{mA}$	$T_C = +25^\circ\text{C}$	20	32	-	V
Collector-Emitter Leakage Current	I_{CES}	$V_{CE} = 250\text{V}$	$T_C = +25^\circ\text{C}$	-	-	5	μA
		$V_{CE} = 250\text{V}$	$T_C = +175^\circ\text{C}$	-	-	250	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 10\text{A}$ $V_{GE} = 4.5\text{V}$	$T_C = +25^\circ\text{C}$	-	1.3	1.6	V
			$T_C = +175^\circ\text{C}$	-	1.25	1.5	V
		$I_C = 20\text{A}$ $V_{GE} = 5.0\text{V}$	$T_C = +25^\circ\text{C}$	-	1.6	2.8	V
			$T_C = +175^\circ\text{C}$	-	1.9	3.5	V
Gate-Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C = 1\text{mA}$ $V_{CE} = V_{GE}$	$T_C = +25^\circ\text{C}$	1.3	1.8	2.3	V
Gate Series Resistance	R_1		$T_C = +25^\circ\text{C}$	-	1.0	-	$\text{k}\Omega$
Gate-Emitter Resistance	R_2		$T_C = +25^\circ\text{C}$	10	17	25	$\text{k}\Omega$
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 10\text{V}$		± 400	± 590	± 1000	μA
Gate-Emitter Breakdown Voltage	BV_{GES}	$I_{GES} = \pm 2\text{mA}$		± 12	± 14	-	V
Current Turn-Off Time-Inductive Load	$t_{D(OFF)I} + t_{F(OFF)I}$	$I_C = 10\text{A}$, $R_G = 25\Omega$, $L = 550\mu\text{H}$, $R_L = 26.4\Omega$, $V_{GE} = 5\text{V}$, $V_{CL} = 300\text{V}$, $T_C = +175^\circ\text{C}$		-	15	30	μs
Inductive Use Test	I_{SCIS}	$L = 2.3\text{mH}$, $V_G = 5\text{V}$, $R_G = 0\Omega$	$T_C = +175^\circ\text{C}$	18	-	-	A
			$T_C = +25^\circ\text{C}$	26	-	-	A
Thermal Resistance	$R_{\theta JC}$			-	-	1.0	$^\circ\text{C/W}$

Typical Performance Curves

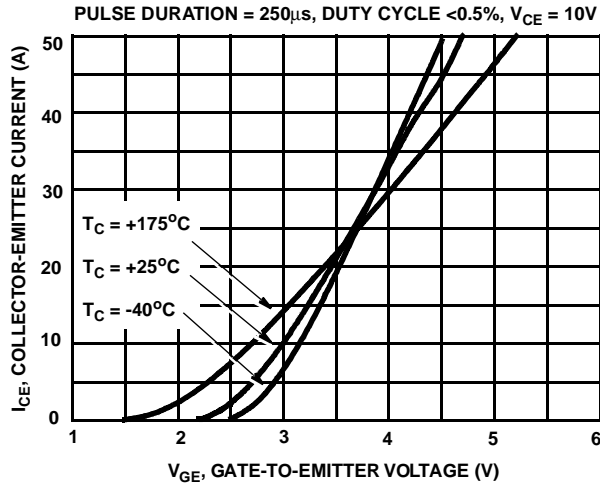


FIGURE 1. TRANSFER CHARACTERISTICS

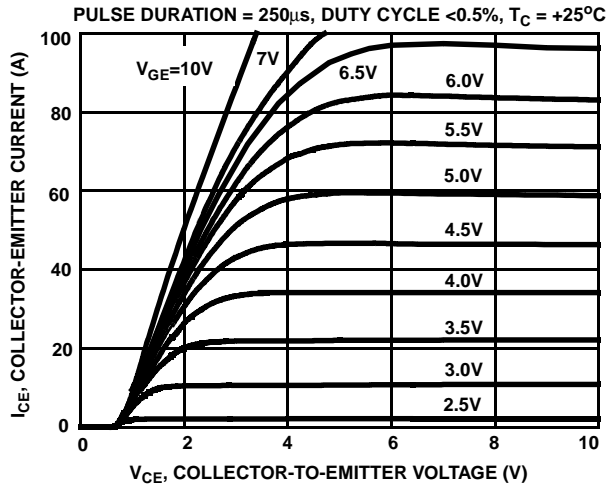


FIGURE 2. SATURATION CHARACTERISTICS

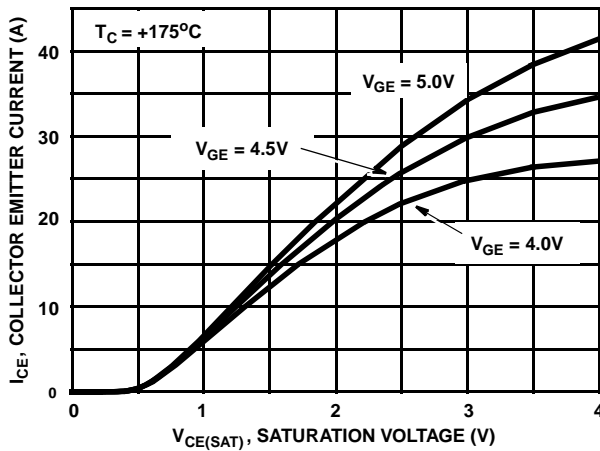


FIGURE 3. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

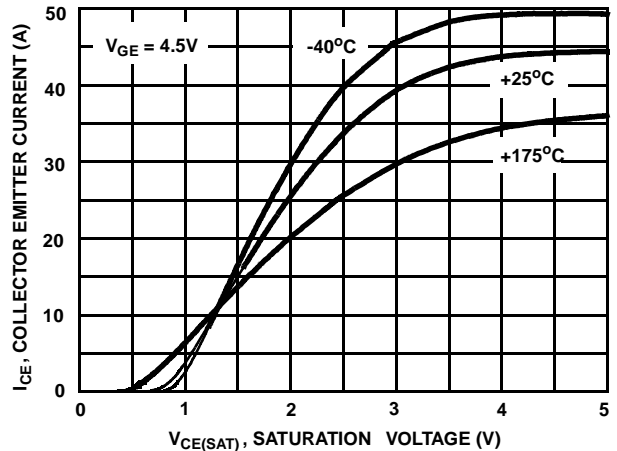


FIGURE 4. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

Typical Performance Curves (Continued)

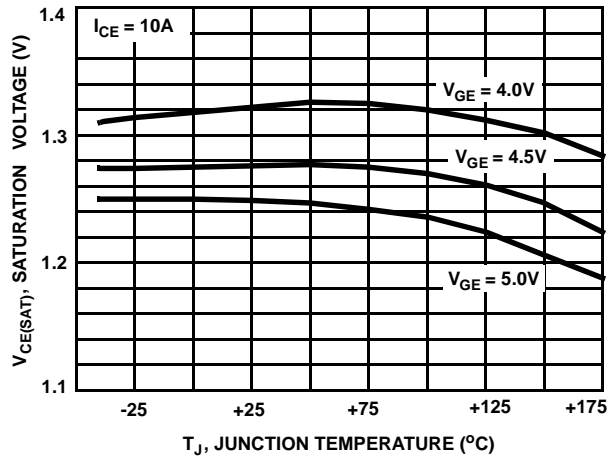


FIGURE 5. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

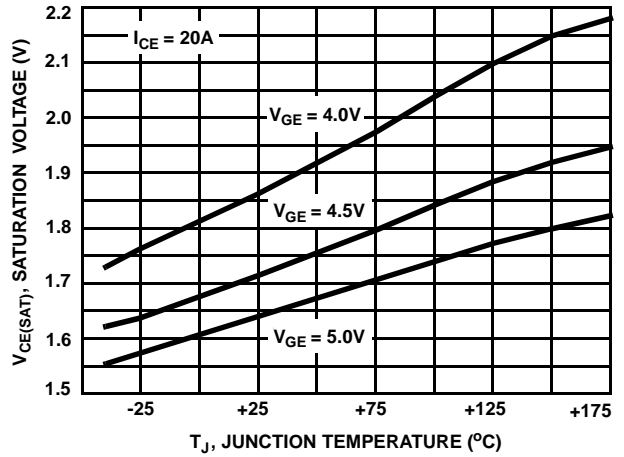


FIGURE 6. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

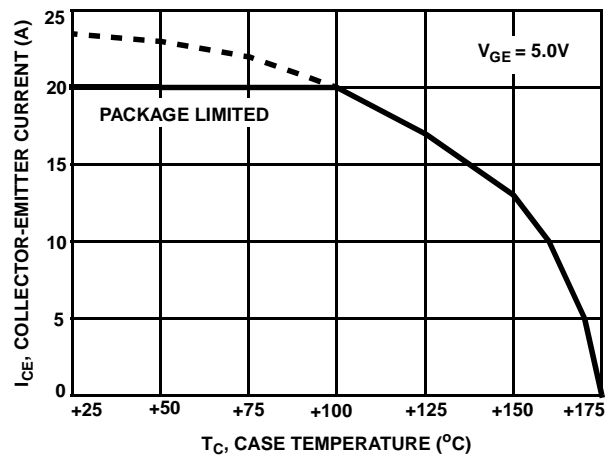


FIGURE 7. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF CASE TEMPERATURE

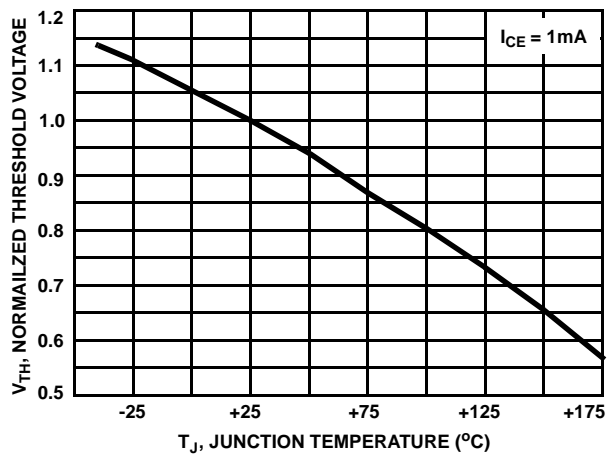


FIGURE 8. NORMALIZED THRESHOLD VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

Typical Performance Curves (Continued)

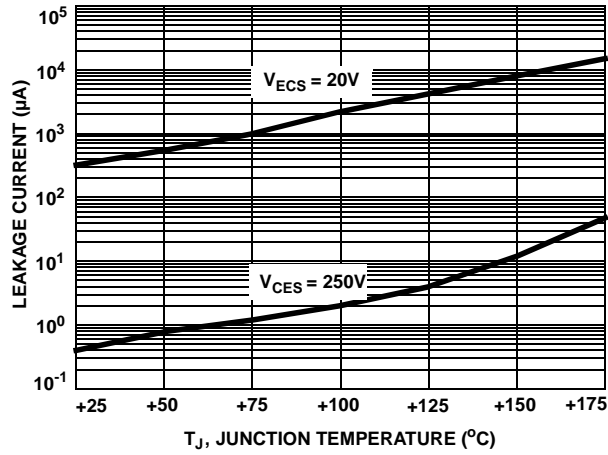


FIGURE 9. LEAKAGE CURRENT AS A FUNCTION OF JUNCTION TEMPERATURE

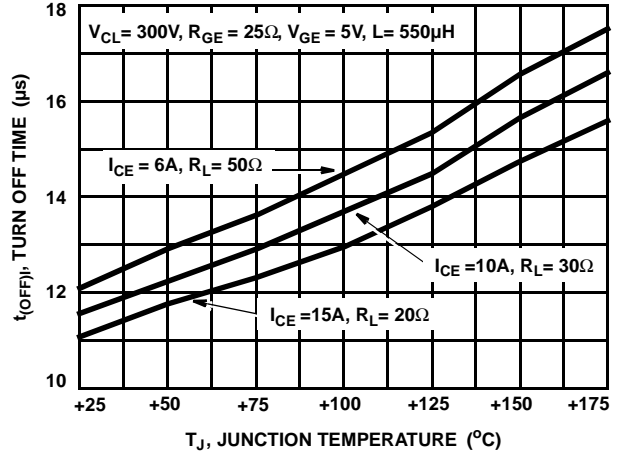


FIGURE 10. TURN-OFF TIME AS A FUNCTION OF JUNCTION TEMPERATURE

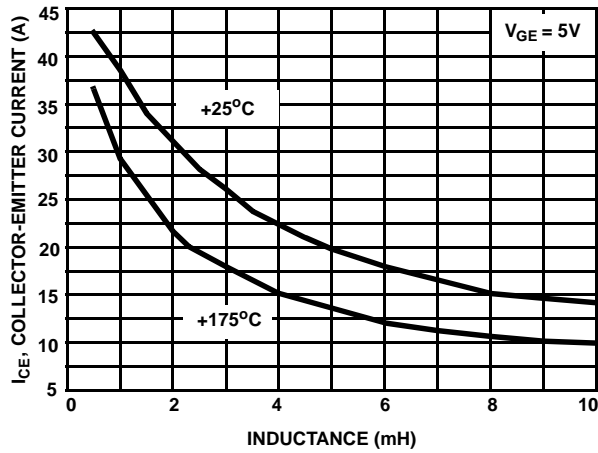


FIGURE 11. SELF CLAMPED INDUCTIVE SWITCHING CURRENT AS A FUNCTION OF INDUCTANCE

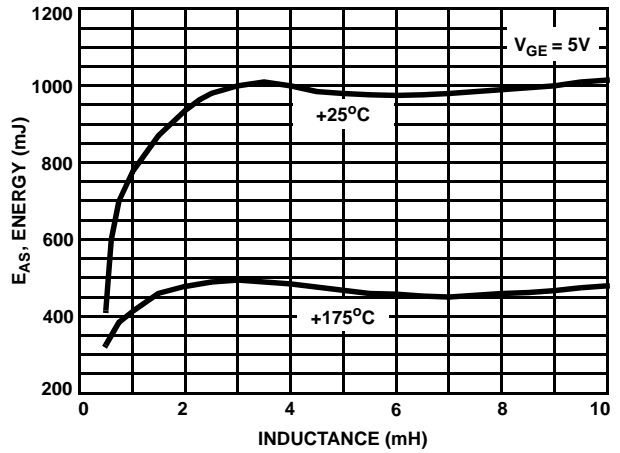


FIGURE 12. SELF CLAMPED INDUCTIVELY SWITCHING ENERGY AS A FUNCTION OF INDUCTANCE

Typical Performance Curves (Continued)

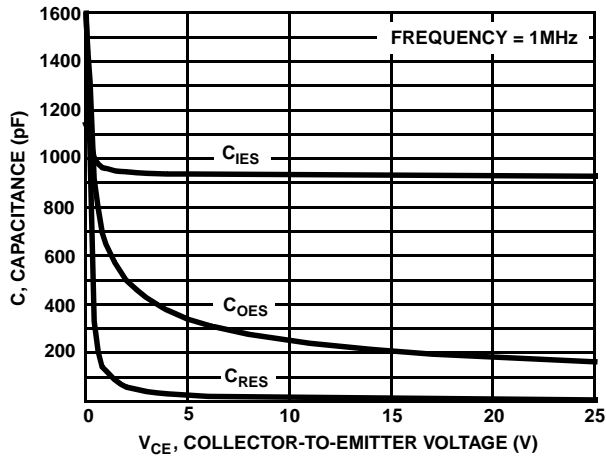


FIGURE 13. CAPACITANCE AS A FUNCTION OF COLLECTOR-EMITTER VOLTAGE

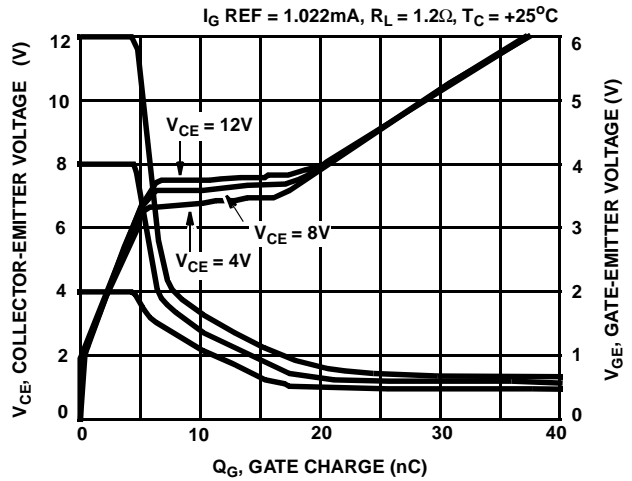


FIGURE 14. GATE CHARGE WAVEFORMS

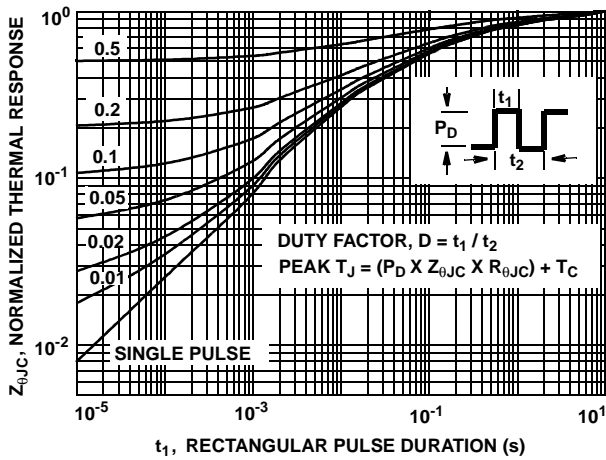


FIGURE 15. NORMALIZED TRANSIENT THERMAL IMPEDANCE, JUNCTION TO CASE

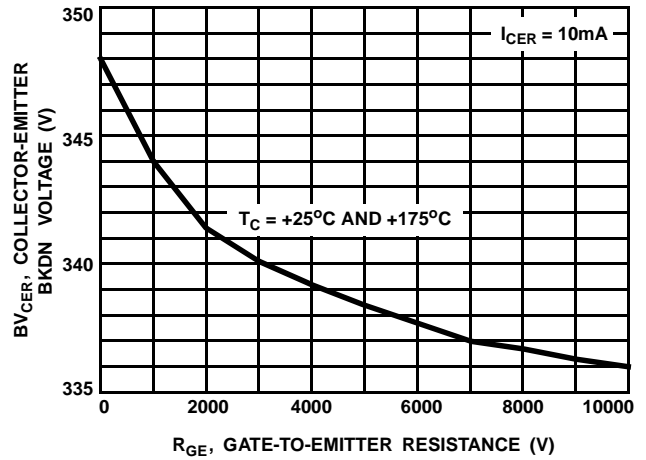


FIGURE 16. BREAKDOWN VOLTAGE AS A FUNCTION OF GATE - Emitter RESISTANCE

Test Circuits

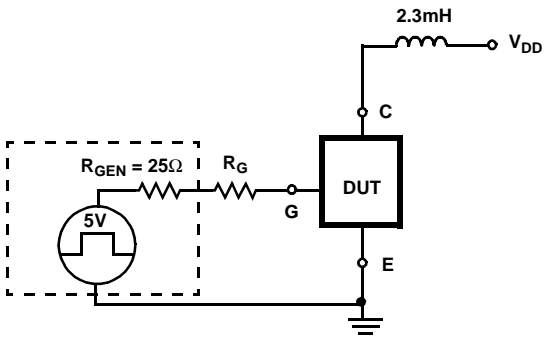


FIGURE 17. USE TEST CIRCUIT

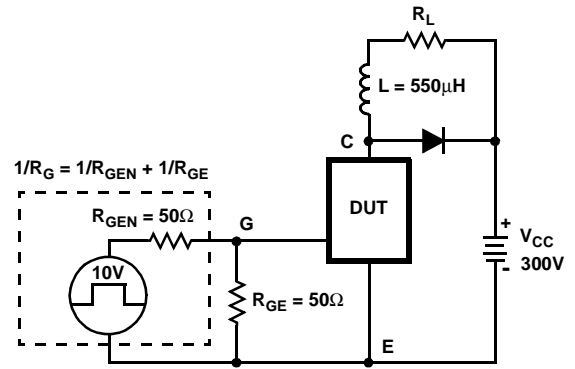


FIGURE 18. INDUCTIVE SWITCHING TEST CIRCUIT

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE _x TM	FAST [®]	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST _r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOMET TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QST TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.